HFA25TB60S



Vishay High Power Products HEXFRED[®] Ultrafast Soft Recovery Diode, 25 A

ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-	
Maximum forward voltage	V _{FM}	I _F = 25 A	See fig. 1	-	1.3	1.7	V
		I _F = 50 A		-	1.5	2.0	
		I _F = 25 A, T _J = 125 °C		-	1.3	1.7	
Maximum reverse		$V_{R} = V_{R}$ rated	See fig. 2	-	1.5	20	μA
leakage current	I _{RM}	T_J = 125 °C, V_R = 0.8 x V_R rated		-	600	2000	
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	55	100	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0 -		nH			

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}/\mu s, V_R = 30 \text{ V}$		-	23	-	
	t _{rr1}	T _J = 25 °C	I _F = 25 A dI _F /dt = 200 A/μs V _R = 200 V	-	50	75	ns
	t _{rr2}	T _J = 125 °C		-	105	160	
Peak recovery current See fig. 6	I _{RRM1}	$T_J = 25 \ ^{\circ}C$		-	4.5	10	A
	I _{RRM2}	T _J = 125 °C		-	8.0	15	
Reverse recovery charge See fig. 7	Q _{rr1}	T _J = 25 °C		-	112	375	nC
	Q _{rr2}	T _J = 125 °C		-	420	1200	
Peak rate of fall recovery current during t _b See fig. 8	dl _{(rec)M} /dt1	T _J = 25 °C		-	250	-	A/µs
	dl _{(rec)M} /dt2	T _J = 125 °C		-	160	-	Αγμο

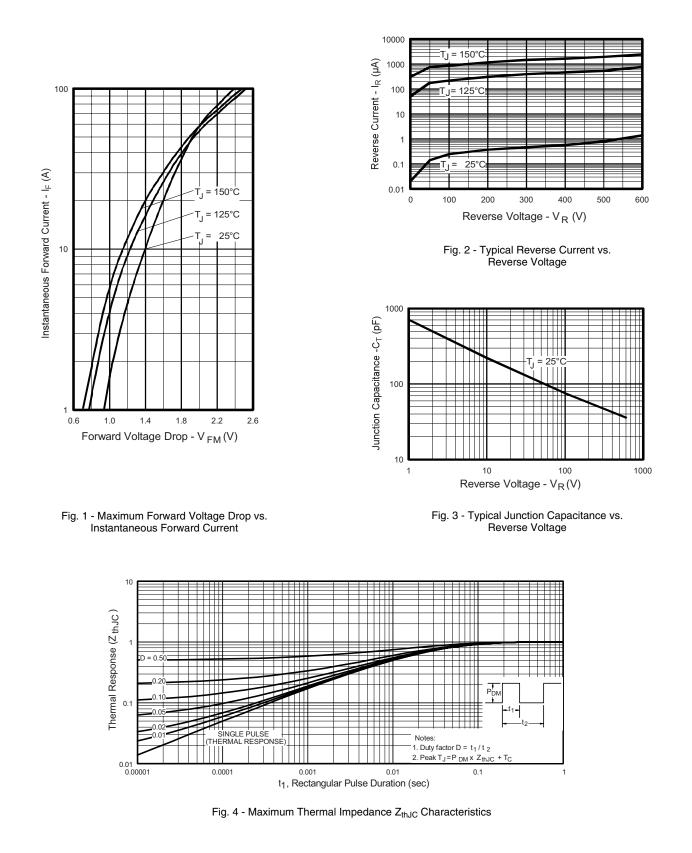
THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R _{thJC}		-	-	1.0	K/W
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	r\/ v v
Weight			-	2.0	-	g
			-	0.07	-	oz.
Marking device		Case style D ² PAK		HFA25	TB60S	



HEXFRED[®]

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Ultrafast Soft Recovery Diode, 25 A



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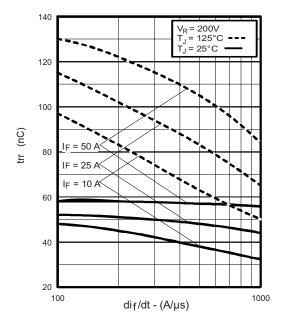
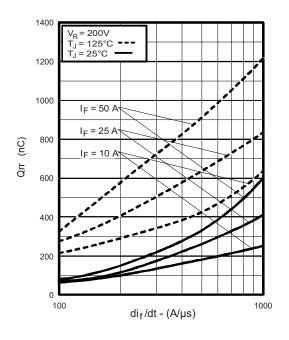


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt



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Fig. 7 - Typical Stored Charge vs. $dI_{\rm F}/dt$

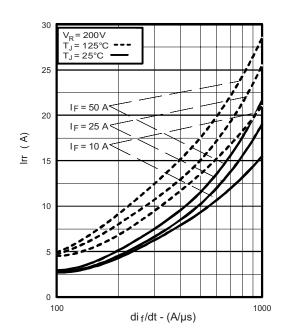


Fig. 6 - Typical Recovery Current vs. dI_F/dt

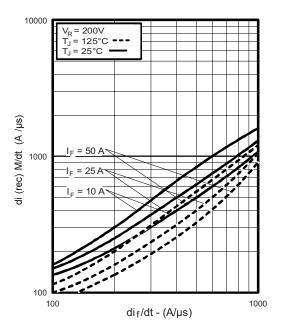


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt



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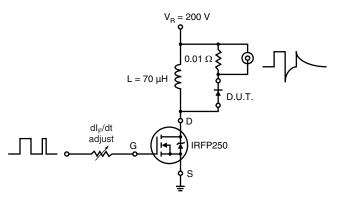


Fig. 9 - Reverse Recovery Parameter Test Circuit

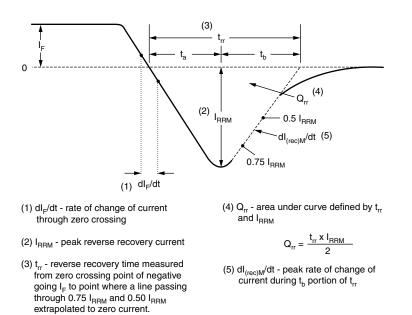


Fig. 10 - Reverse Recovery Waveform and Definitions

LINKS TO RELATED DOCUMENTS				
Dimensions	http://www.vishay.com/doc?95046			
Part marking information	http://www.vishay.com/doc?95054			
Packaging information	http://www.vishay.com/doc?95032			



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